

## 1. General description

Planar passivated three quadrant triac in a SOT428 (DPAK) surface-mountable plastic package. This "series D" triac balances the requirements of commutation performance and gate sensitivity and is intended for interfacing with low power drivers and logic ICs including microcontrollers.

## 2. Features and benefits

- 3Q technology for improved noise immunity
- Direct gate triggering from low power drivers and logic ICs
- High blocking voltage capability
- High commutation capability with very sensitive gate
- Planar passivated for voltage ruggedness and reliability
- Surface-mountable package
- Triggering in three quadrants only
- Very sensitive gate for easy logic level triggering

## 3. Applications

- AC solenoids
- General purpose motor control circuits
- Home appliances

## 4. Quick reference data

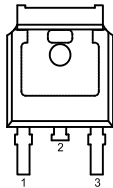
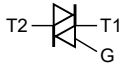
Table 1. Quick reference data

| Symbol                        | Parameter                            | Conditions   | Min | Typ | Max | Unit |
|-------------------------------|--------------------------------------|--|-----|-----|-----|------|
| $V_{DRM}$                     | repetitive peak off-state voltage    |  | -   | -   | 600 | V    |
| $I_{T(RMS)}$                  | RMS on-state current                 | full sine wave; $T_{mb} \leq 107\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a> | -   | -   | 4   | A    |
| $I_{TSM}$                     | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>  | -   | -   | 25  | A    |
|                               |                                      | full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 16.7\text{ ms}$  | -   | -   | 27  | A    |
| $T_j$                         | junction temperature                 |  | -   | -   | 125 | °C   |
| <b>Static characteristics</b> |                                      |  |     |     |     |      |
| $I_{GT}$                      | gate trigger current                 | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>                     | -   | -   | 5   | mA   |
|                               |                                      | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>                     | -   | -   | 5   | mA   |

| Symbol                         | Parameter                             | Conditions  | Min | Typ | Max | Unit             |
|--------------------------------|---------------------------------------|---|-----|-----|-----|------------------|
|                                |                                       | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ °C}$ ; Fig. 7   | -   | -   | 5   | mA               |
| $I_H$                          | holding current                       | $V_D = 12\text{ V}$ ; $T_j = 25\text{ °C}$ ; Fig. 9   | -   | -   | 6   | mA               |
| $V_T$                          | on-state voltage                      | $I_T = 5\text{ A}$ ; $T_j = 25\text{ °C}$ ; Fig. 10   | -   | 1.4 | 1.7 | V                |
| <b>Dynamic characteristics</b> |                                       |   |     |     |     |                  |
| $dV_D/dt$                      | rate of rise of off-state voltage     | $V_{DM} = 402\text{ V}$ ; $T_j = 125\text{ °C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit             | 20  | -   | -   | V/ $\mu\text{s}$ |
| $dI_{com}/dt$                  | rate of change of commutating current | $V_D = 400\text{ V}$ ; $T_j = 125\text{ °C}$ ; $I_{T(RMS)} = 4\text{ A}$ ; $dV_{com}/dt = 10\text{ V}/\mu\text{s}$ ; gate open circuit  | 1.1 | -   | -   | A/ms             |
|                                |                                       | $V_D = 400\text{ V}$ ; $T_j = 125\text{ °C}$ ; $I_{T(RMS)} = 4\text{ A}$ ; $dV_{com}/dt = 0.1\text{ V}/\mu\text{s}$ ; gate open circuit | 4.5 | -   | -   | A/ms             |

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                    | Simplified outline  | Graphic symbol  |
|-----|--------|--------------------------------|---|---|
| 1   | T1     | main terminal 1                |  <p><b>DPAK (SOT428)</b></p> |  <p>sym051</p> |
| 2   | T2     | main terminal 2                |   |   |
| 3   | G      | gate                           |   |   |
| mb  | T2     | mounting base; main terminal 2 |   |   |

## 6. Ordering information

Table 3. Ordering information

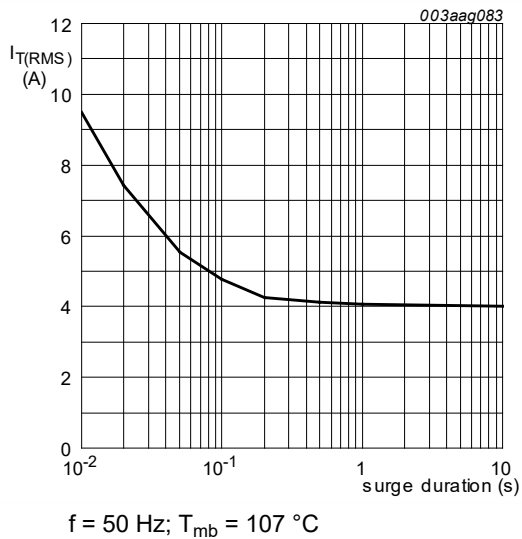
| Type number  | Package |   |         |
|--------------|---------|---|---------|
|              | Name    | Description   | Version |
| BTA204S-600D | DPAK    | plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped) | SOT428  |

## 7. Limiting values

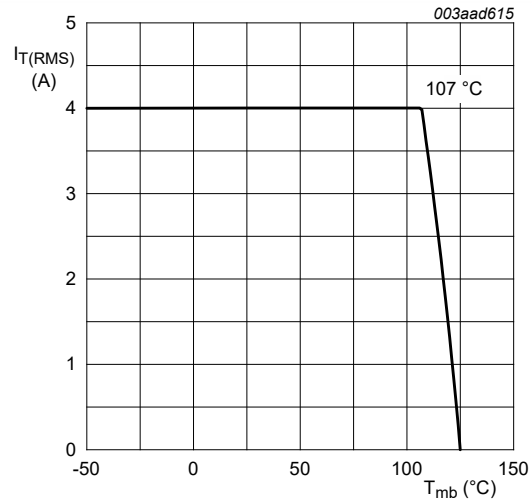
**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol       | Parameter                            | Conditions   | Min | Max | Unit             |
|--------------|--------------------------------------|--|-----|-----|------------------|
| $V_{DRM}$    | repetitive peak off-state voltage    |  | -   | 600 | V                |
| $I_{T(RMS)}$ | RMS on-state current                 | full sine wave; $T_{mb} \leq 107\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>       | -   | 4   | A                |
| $I_{TSM}$    | non-repetitive peak on-state current | full sine wave; $T_{j(\text{init})} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a> | -   | 25  | A                |
|              |                                      | full sine wave; $T_{j(\text{init})} = 25\text{ °C}$ ; $t_p = 16.7\text{ ms}$   | -   | 27  | A                |
| $I^2t$       | $I^2t$ for fusing                    | $t_p = 10\text{ ms}$ ; SIN   | -   | 3.1 | A <sup>2</sup> s |
| $di_T/dt$    | rate of rise of on-state current     | $I_G = 0.2\text{ A}$   | -   | 100 | A/ $\mu$ s       |
| $I_{GM}$     | peak gate current                    |  | -   | 2   | A                |
| $P_{GM}$     | peak gate power                      |  | -   | 5   | W                |
| $P_{G(AV)}$  | average gate power                   | over any 20 ms period  | -   | 0.5 | W                |
| $T_{stg}$    | storage temperature                  |  | -40 | 150 | °C               |
| $T_j$        | junction temperature                 |  | -   | 125 | °C               |



**Fig. 1. RMS on-state current as a function of surge duration; maximum values**



**Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values**

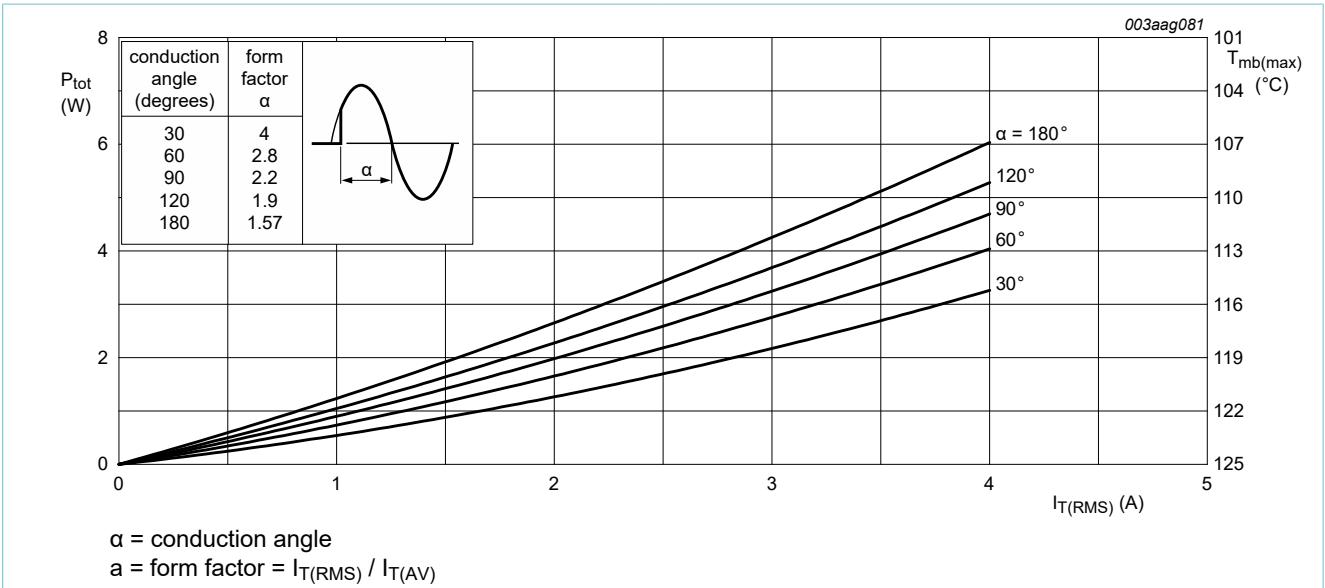


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

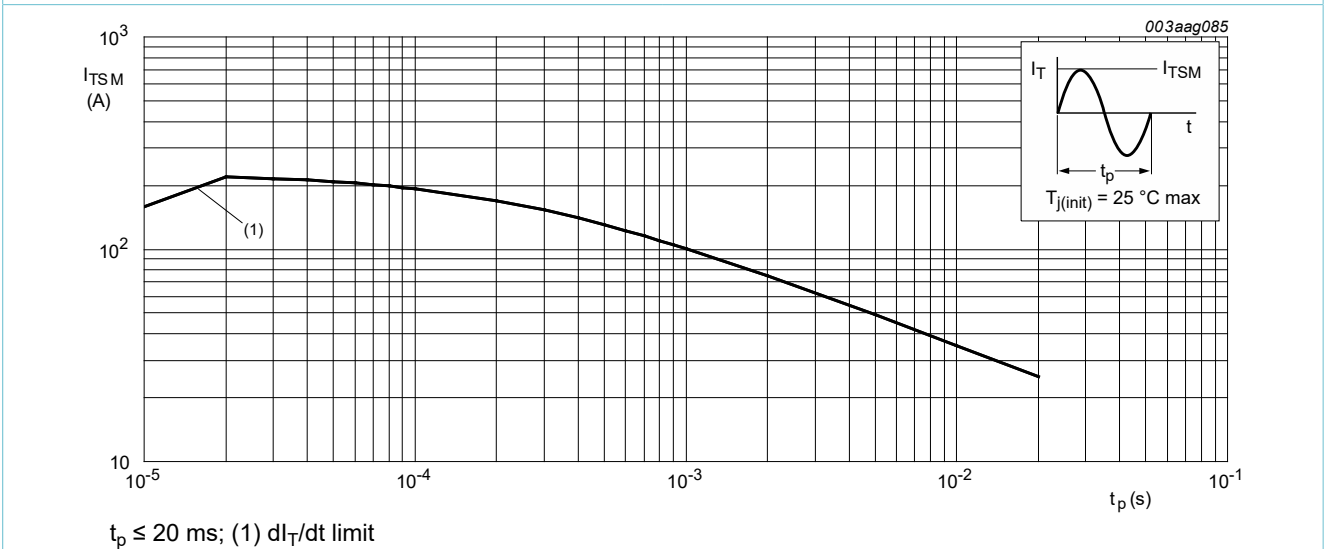
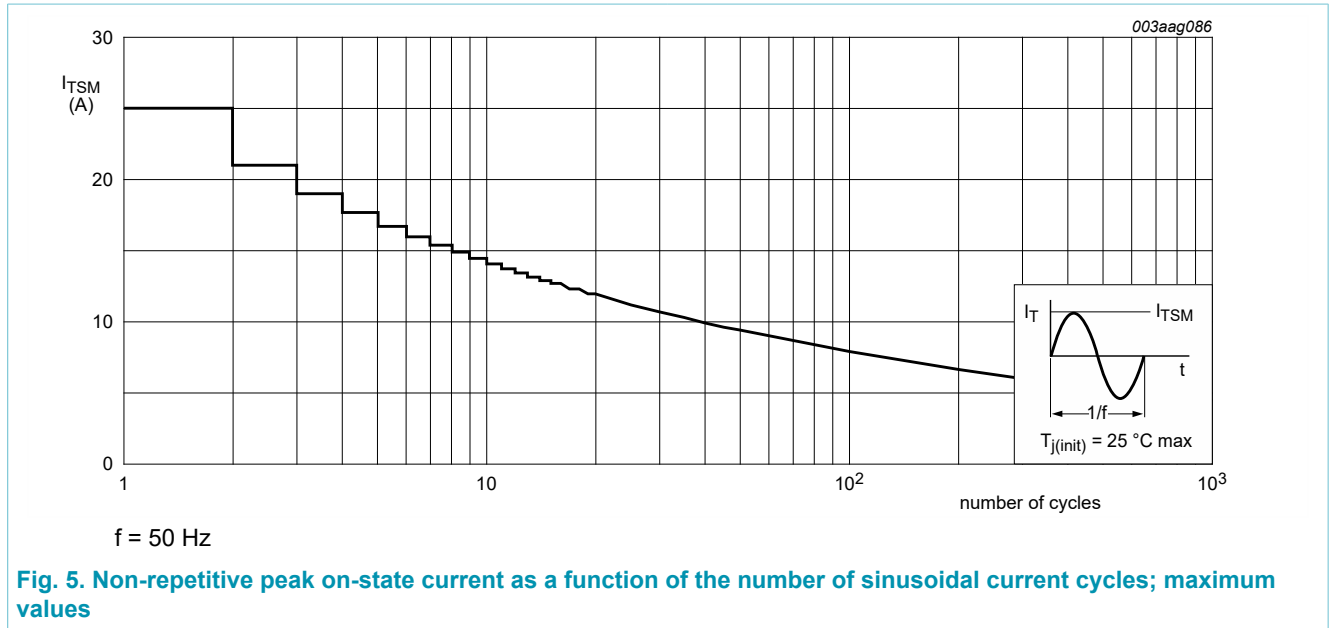


Fig. 4. Non-repetitive peak on-state current as a function of pulse width; maximum values



## 8. Thermal characteristics

Table 5. Thermal characteristics

| Symbol         | Parameter  | Conditions                          | Min | Typ | Max | Unit |
|----------------|--|-------------------------------------|-----|-----|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base    | full cycle; <a href="#">Fig. 6</a>  | -   | -   | 3   | K/W  |
|                |  | half cycle; <a href="#">Fig. 6</a>  | -   | -   | 3.7 | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient free air | printed circuit board (FR4) mounted | -   | 75  | -   | K/W  |



## 9. Characteristics

Table 6. Characteristics

| Symbol                         | Parameter                             | Conditions   | Min  | Typ | Max | Unit       |
|--------------------------------|---------------------------------------|--|------|-----|-----|------------|
| <b>Static characteristics</b>  |                                       |  |      |     |     |            |
| $I_{GT}$                       | gate trigger current                  | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>                                      | -    | -   | 5   | mA         |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>                                      | -    | -   | 5   | mA         |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>                                      | -    | -   | 5   | mA         |
| $I_L$                          | latching current                      | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G+;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 8</a>                                      | -    | -   | 6   | mA         |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G-;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 8</a>                                      | -    | -   | 9   | mA         |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 8</a>                                      | -    | -   | 6   | mA         |
| $I_H$                          | holding current                       | $V_D = 12\text{ V}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>  | -    | -   | 6   | mA         |
| $V_T$                          | on-state voltage                      | $I_T = 5\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 10</a>  | -    | 1.4 | 1.7 | V          |
| $V_{GT}$                       | gate trigger voltage                  | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ °C}$ ;<br><a href="#">Fig. 11</a>   | -    | 0.7 | 1   | V          |
|                                |                                       | $V_D = 400\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 125\text{ °C}$ ;<br><a href="#">Fig. 11</a>   | 0.25 | 0.4 | -   | V          |
| $I_D$                          | off-state current                     | $V_D = 600\text{ V}$ ; $T_j = 125\text{ °C}$   | -    | 0.1 | 0.5 | mA         |
| <b>Dynamic characteristics</b> |                                       |  |      |     |     |            |
| $dV_D/dt$                      | rate of rise of off-state voltage     | $V_{DM} = 402\text{ V}$ ; $T_j = 125\text{ °C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit                | 20   | -   | -   | V/ $\mu$ s |
| $dI_{com}/dt$                  | rate of change of commutating current | $V_D = 400\text{ V}$ ; $T_j = 125\text{ °C}$ ; $I_{T(RMS)} = 4\text{ A}$ ;<br>$dV_{com}/dt = 10\text{ V}/\mu\text{s}$ ; gate open circuit  | 1.1  | -   | -   | A/ms       |
|                                |                                       | $V_D = 400\text{ V}$ ; $T_j = 125\text{ °C}$ ; $I_{T(RMS)} = 4\text{ A}$ ;<br>$dV_{com}/dt = 0.1\text{ V}/\mu\text{s}$ ; gate open circuit | 4.5  | -   | -   | A/ms       |



- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

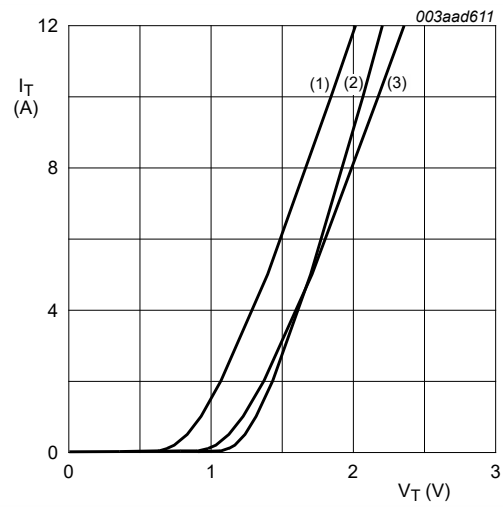
Fig. 7. Normalized gate trigger current as a function of junction temperature



Fig. 8. Normalized latching current as a function of junction temperature



Fig. 9. Normalized holding current as a function of junction temperature



$V_o = 1.27 \text{ V}; R_s = 0.091 \Omega$

- (1)  $T_j = 125 \text{ }^\circ\text{C}$ ; typical values
- (2)  $T_j = 125 \text{ }^\circ\text{C}$ ; maximum values
- (3)  $T_j = 25 \text{ }^\circ\text{C}$ ; maximum values

Fig. 10. On-state current as a function of on-state voltage





Fig. 11. Normalized gate trigger voltage as a function of junction temperature

10. Package outline



Fig. 12. Package outline DPAK (SOT428)

# 11. Legal information

## Data sheet status

| Document status [1][2]         | Product status [3] | Definition  |
|--------------------------------|--------------------|---|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
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- [1] Please consult the most recently issued document before initiating or completing a design.
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